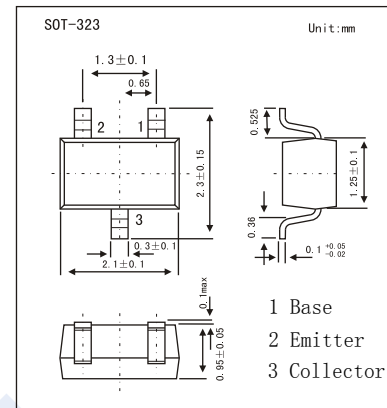


NPN Transistors

2SC3930

■ Features

- Optimum for RF amplification of FM/AM radios.
- High transition frequency fr.
- Complementary to 2SA1532



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	30	V
Collector - Emitter Voltage	V _{CEO}	20	
Emitter - Base Voltage	V _{EBO}	5	
Collector Current - Continuous	I _c	30	mA
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = 100 uA, I _E = 0	30			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = 1 mA, I _B = 0	20			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 uA, I _c = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 25V, I _E = 0			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V, I _c = 0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =10 mA, I _B =1mA			1	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =10 mA, I _B =1mA			1.2	
DC current gain	h _{FE}	V _{CE} = 10V, I _c = 1mA	70		220	
Noise figure	NF	V _{CB} = 10V, I _E = -1mA, f=5MHz		2.8	4	dB
Reverse transfer impedance	Z _{rb}	V _{CB} = 10V, I _E = -1mA, f=2MHz		22	50	Ω
Common emitter reverse transfer capacitance	C _{re}	V _{CE} = 10V, I _c = 1mA, f=10.7MHz		0.9	1.5	pF
Transition frequency	f _T	V _{CE} = 10V, I _E = -1mA, f=200MHz	150	250		MHz

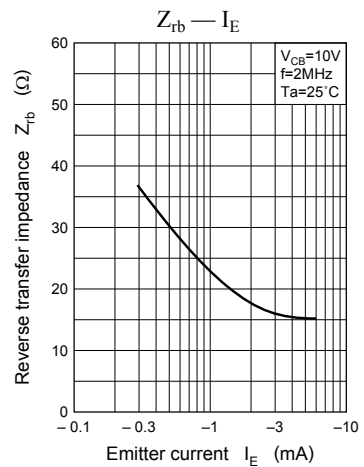
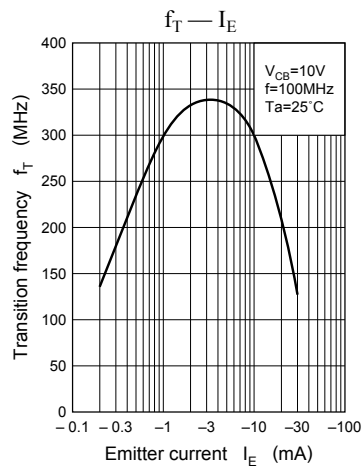
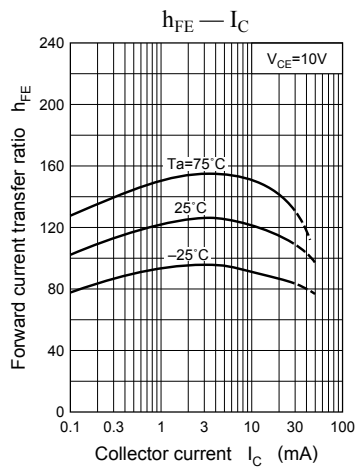
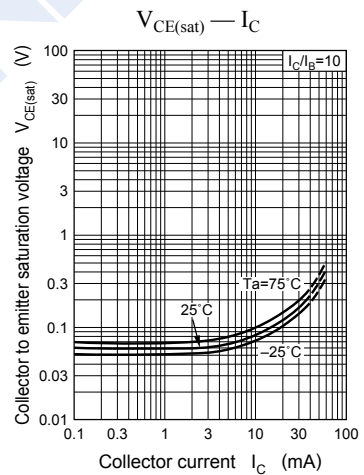
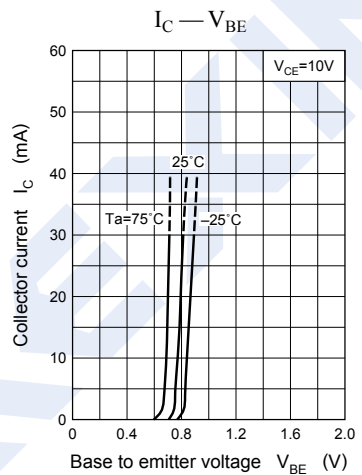
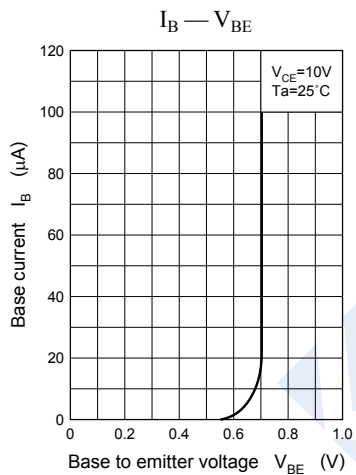
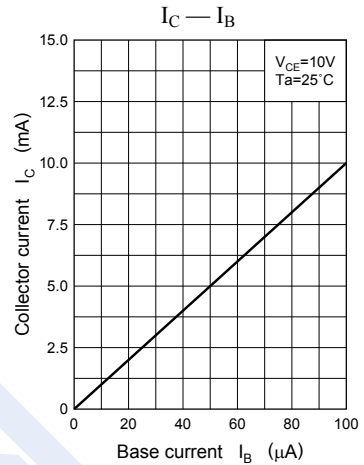
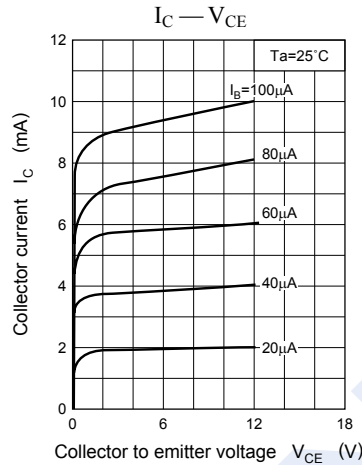
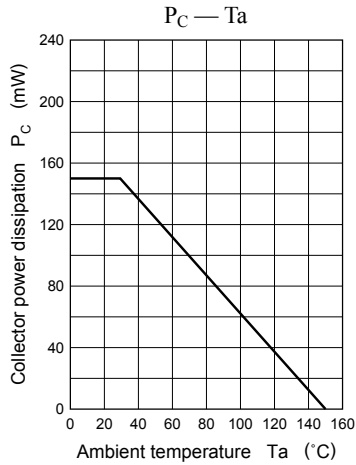
■ Classification of h_{FE}

Type	2SC3930-B	2SC3930-C
Range	70-140	110-220
Marking	VB	VC

NPN Transistors

2SC3930

Typical Characteristics



NPN Transistors

2SC3930

■ Typical Characteristics

